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Contents

vii	Conference Committee
	P-TYPE OXIDES
12887 02	Li-doped IrO ₂ /Si heterojunctions for CMOS-integrated optoelectronics [12887-2]
12887 03	Nickel oxide hole transport layer engineering for mitigation of photo segregation in mixed halide organic-inorganic lead halide perovskites [12887-4]
	GALLIUM OXIDE I
12887 04	Split and unrelaxed Ga vacancies in β -Ga ₂ O ₃ (Invited Paper) [12887-7]
	GALLIUM OXIDE II
12887 05	Thermal properties of Ga_2O_3 thin films and devices prepared on sapphire and SiC substrates by liquid-injection MOCVD (Invited Paper) [12887-12]
12887 06	Impacts of device processing on contact interfaces to (010) β-Ga ₂ O ₃ [12887-13]
	GALLIUM OXIDE III
12887 07	Crystal growth and power device applications of β -Ga ₂ O ₃ (Invited Paper) [12887-16]
	GALLIUM OXIDE IV
12887 08	O-H centers in β -Ga ₂ O ₃ with a Ga(1) vacancy at their core (Invited Paper) [12887-21]
	GALLIUM OXIDE V
12887 09	Heteroepitaxy and annealing studies of orthorhombic gallium oxide films on nanostructured AIN templates (Invited Paper) [12887-24]

	GALLIUM OXIDE VI
12887 0A	Chromium doped gallium oxide nanowire-based thermometer and the study of the anisotropic refractive index temperature dependence (Invited Paper) [12887-26]
12887 OB	Modeling of the gate leakage in MOSFETs with Al_2O_3/β -Ga ₂ O ₃ gate stack (Invited Paper) [12887-29]
12887 OC	Heterogenous integration of gallium oxide with diamond and SiC (Invited Paper) [12887-30]
	VARIOUS OXIDES/APPLICATIONS I
12887 OD	Lithium niobate long-period waveguide gratings integrated with bismuth ferrite (BiFeO3) resistive random access memory [12887-31]
12887 OE	Material characterization of silicon dioxide cladding for photonic devices [12887-35]
	PHOTODETECTORS
12887 OF	Bismuth ferrite (BiFeO3)-based metal-semiconductor-metal photodetectors realized by the design of the experiments approach [12887-37]
	VARIOUS OXIDES/APPLICATIONS II
12887 0G	High quality ZnMgAlO thin films by ultrasonic spray pyrolysis: tuning of optoelectronic properties for use as TCO, window layer, and buffer layer in all-oxide solar cells [12887-42]
	VARIOUS OXIDES/APPLICATIONS V
12887 OH	Layer transfer technique of epitaxial rutile TiO2 thin films for photonic applications (Invited Paper) [12887-56]
	VARIOUS OXIDES/APPLICATIONS VI
12887 01	Plasma conduction mechanism in topological insulators [12887-57]
12887 OJ	Comparison of PLD-grown p-NiO/n-Ga ₂ O ₃ heterojunctions on bulk single crystal β -Ga ₂ O ₃ and r-plane sapphire substrates [12887-3]

12887 0K The path to low temperature crack-free high refractive index inorganic thin films [12887-64]

POSTER SESSION

- 12887 OL A solution-processed p-type CuAlO₂ thin film and its applications in gas sensing at room temperature [12887-59]
- 12887 0M Chemically induced dynamic polarization by magnetic field on nanoionic photocatalysis via 2-propanol oxidation [12887-60]
- 12887 ON Superconducting crystal dense plasma parameters [12887-61]
- 12887 00 Comparative study of ZnO and WO₃ thin films grown by pulsed laser deposition at similar substrate temperatures [12887-62]
- 12887 OP Use of yttria-stabilised zirconia substrates for zinc oxide mediated epitaxial lift-off of superior yttria-stabilised zirconia thin films [12887-66]

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